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# АПвЭгаАкП-20 1x1000 ТУ У 31.3-00214534-017-2003

Single-core power cables with aluminium conductor, with XLPE, aluminium-wire armoured, with longitudinal and transverse screen sealing and polyethylene outer sheath

Due to non-magnetic armour, cables operate at AC

Technical cable requirements correspond to IEC 60502-2

Cables are used for laying:

- · in places, where small mechanical impacts on cable are possible, including tensile forces
- · in soil (trenches)
- · in damp, partially flooded premises
- · in ground with high humidity
- · in non-navigable waters
- in the air, including cable structures, if provided the additional fire protection

It is possible to manufacture cable with a segmented conductor

It is possible to manufacture cables with extruded semiconductor layer along outer sheath.

Order entry example:

АПвЭгаАкП-П-20 1х1000/70 ТУ У 31.3-00214534-017-2003

An extruded semiconductor layer along outer sheath ensures the correct testing of cable line with sections of underground laying in polymer pipes.

It is possible to manufacture cables with an integrated fiber-optic module.

Order entry example:

АПвЭгаАкП-20 1x1000/70 (ОМ) ТУ У 31.3-00214534-017-2003

In conjunction with the DTS system, the integrated fiber-optic module can act as a distributed cable line temperature sensor.

It is possible to manufacture cable with sealed conductor.

Order entry example:

АПвЭгаАкП-20 1х1000/70 (г) ТУ У 31.3-00214534-017-2003







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## **TECHNICAL SPECIFICATIONS**

kV	20
kV	24
mm²	1 x 1000
mm	5.5
mm²	70
kA	14.2
kA	94
Α	1214
Α	1315
Α	736
Α	717
рС	6
° C	+90
° C	+130
° C	+250
° C	-60 +50
mm	1152
mm	72
kg/km	6540
m, t	# 25УД-90: 583 • 5.4
	kV mm² mm mm² kA  kA  A A A A PC  ° C ° C ° C mm mm kg/km

#### Notes:

When ordering it is neccesary to agree the factory length of the product with the manufacturer

<sup>\*</sup> Long permissible current loads are calculated for the following conditions: conductor temperature 90 °C, air temperature 30 °C, soil temperature 20 °C, thermal resistivity of soil 1.5 °K • m/W, laying depth in the soil 0.8 m, while laying in flat formation the distance between cables in clear is equal to the cable diameter, while laying in trefoil formation cables are laid side by side, shields are earthed on both ends of the line

<sup>\*\*</sup> The external diameter may differ from the rated up to  $\pm$  10 %

<sup>\*\*\*</sup> Отклонение фактической массы брутто от указанного значения может составлять ± 7 %



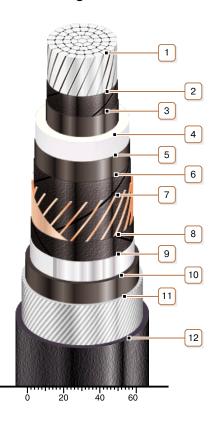




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### **CONSTRUCTION**

- 1. Aluminium multiwire compacted conductor
- · It is possible to manufacture cable with a segmented conductor
- · It is possible to manufacture cable with sealed conductor.
- 2. Lapping layer of semiconductive swellable tape
- 3. Inner extruded semiconducting layer
- 4. XLPE insulation
- 5. Outer extruded semiconducting layer
- 6. Lapping layer of semiconductive swellable tape
- 7. Copper screen
- 8. Lapping layer of semiconductive swellable tape
- 9. Alumopolymer tape
- 10. Extruded bedding of polyethylene
- 11. Aluminium-wire armour
- 12. Outer sheath of polyethylene or polyethylene copolymer

Note: It is possible to manufacture cable with extruded semiconductor layer along outer sheath